

A SURFACE MOUNTABLE MEMBRANE SUPPORTED FILTER

M. CHATRAS *

P. BLONDY *

O. VENDIER **

J.L CAZAUX **

*** IRCOM (UMR CNRS 6615)**

123 Av A. Thomas - 87000 LIMOGES - FRANCE

**** ALCATEL SPACE INDUSTRIES**

26 Av J.F Champollion - 31100 TOULOUSE - FRANCE

chatras@ircom.unilim.fr

OUTLINE OF THE TALK

1) MICRO-MACHINED FILTER

WET ETCHING PROCESS

Q_0 MEASUREMENT

NARROW BAND FILTER

2) SURFACE MOUNTABLE FILTER

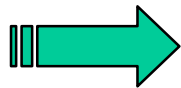
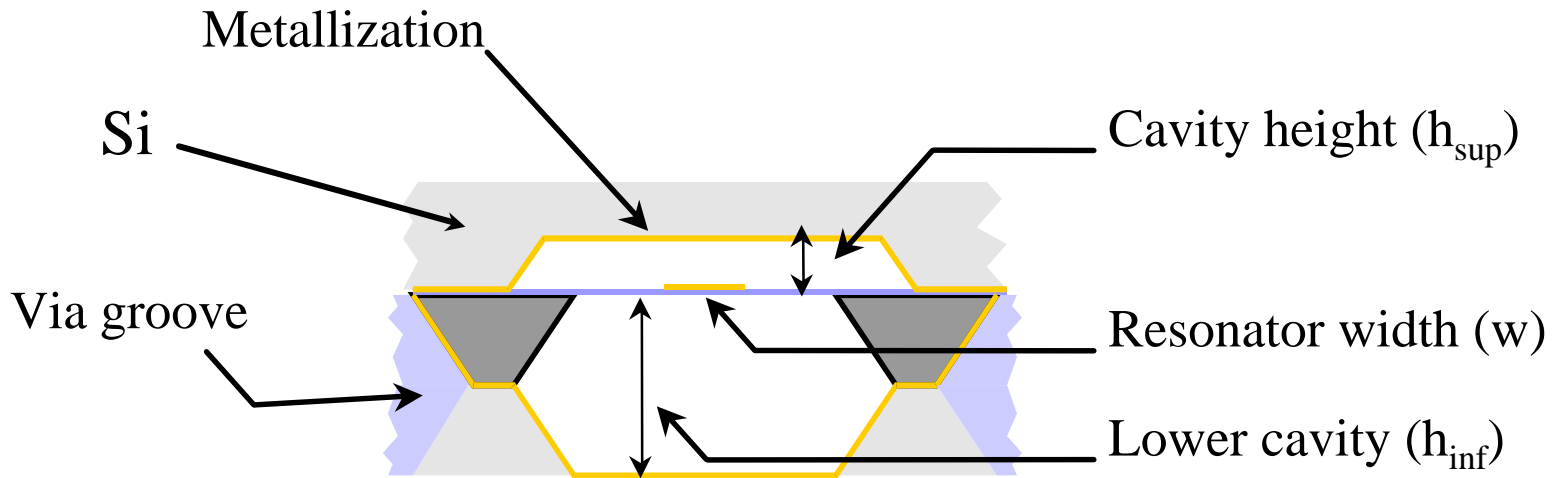
DESCRIPTION OF THE STRUCTURE

3) A 2 POLE 30 GHz MICRO-STRIP FILTER

DESIGN AND FABRICATION

MICRO-MACHINING OVERVIEW

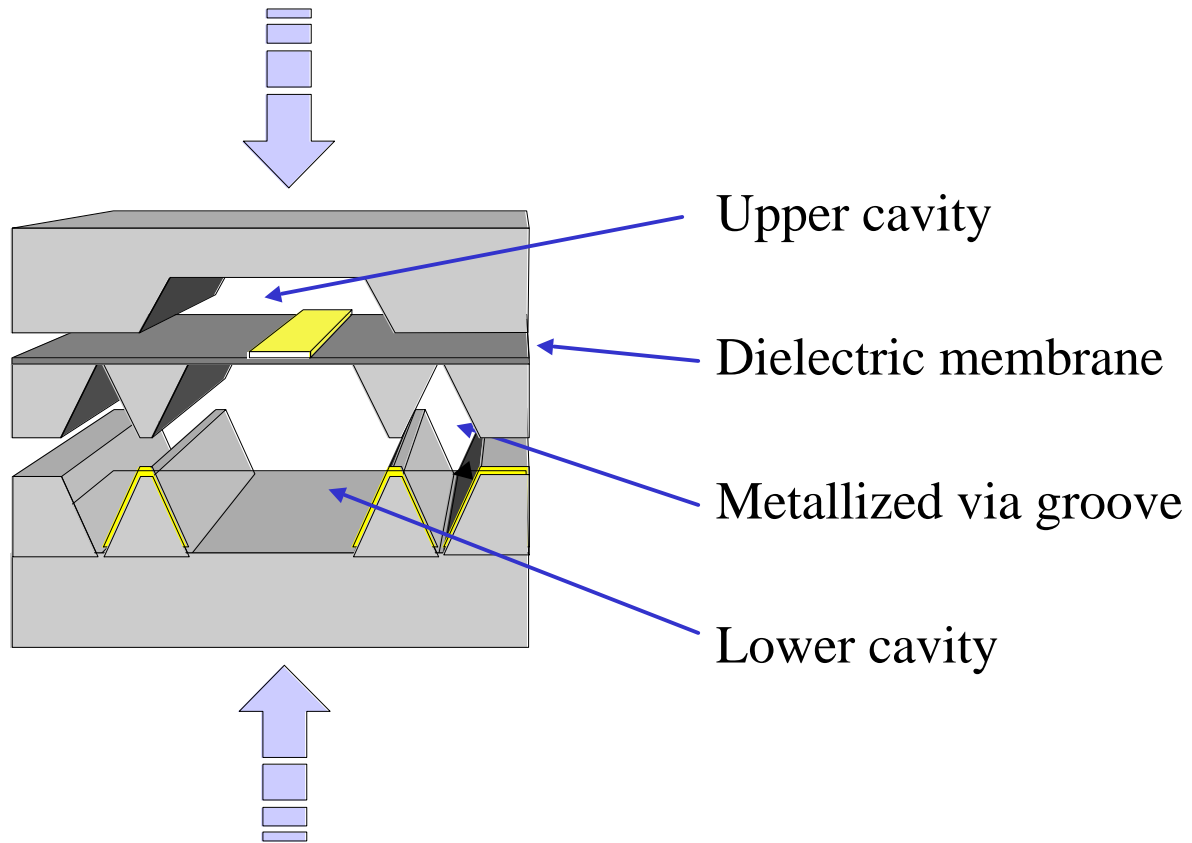
TRANSVERSE SECTION



ASSOCIATION OF 2 CAVITIES

ASSEMBLY

FABRICATION OF 2 CAVITIES WITH 3 MICROMACHINED SUBSTRATES



MICRO-MACHINING OVERVIEW

☺ ADVANTAGES

PLANAR SOLUTION

SMALL SIZE

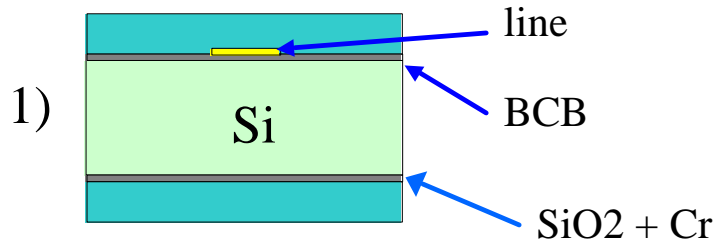
LOW COST

NO DISPERSION OR RADIATION

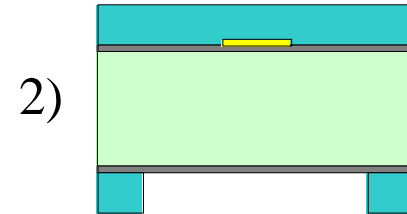
HIGH QUALITY FACTOR (600)

☹ **NEED OF TRANSITION TO CONNECT IT**

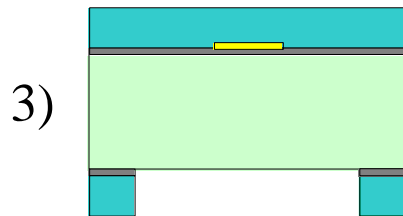
FABRICATION PROCESS



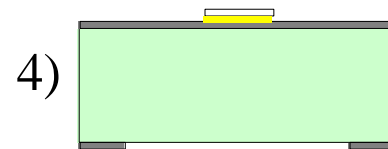
deposit of a resin layer in the upper and lower part



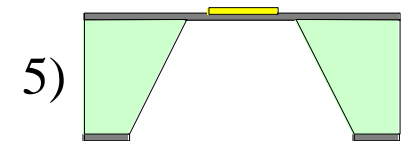
Exposure of the resin in the lower part



etching of the mask level in the lower part



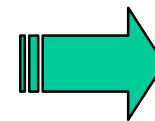
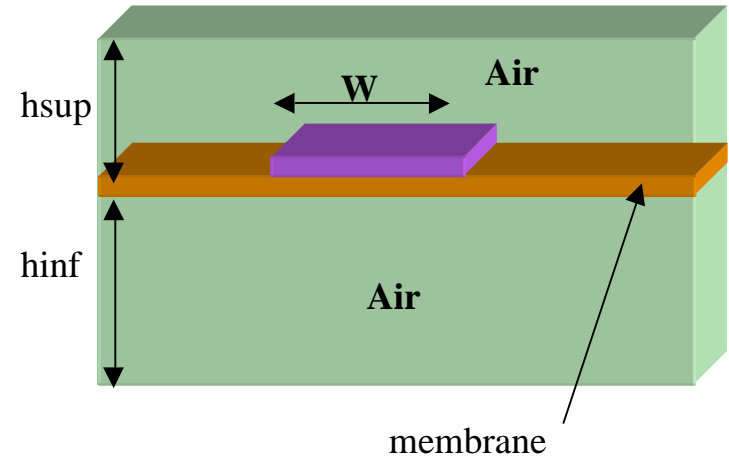
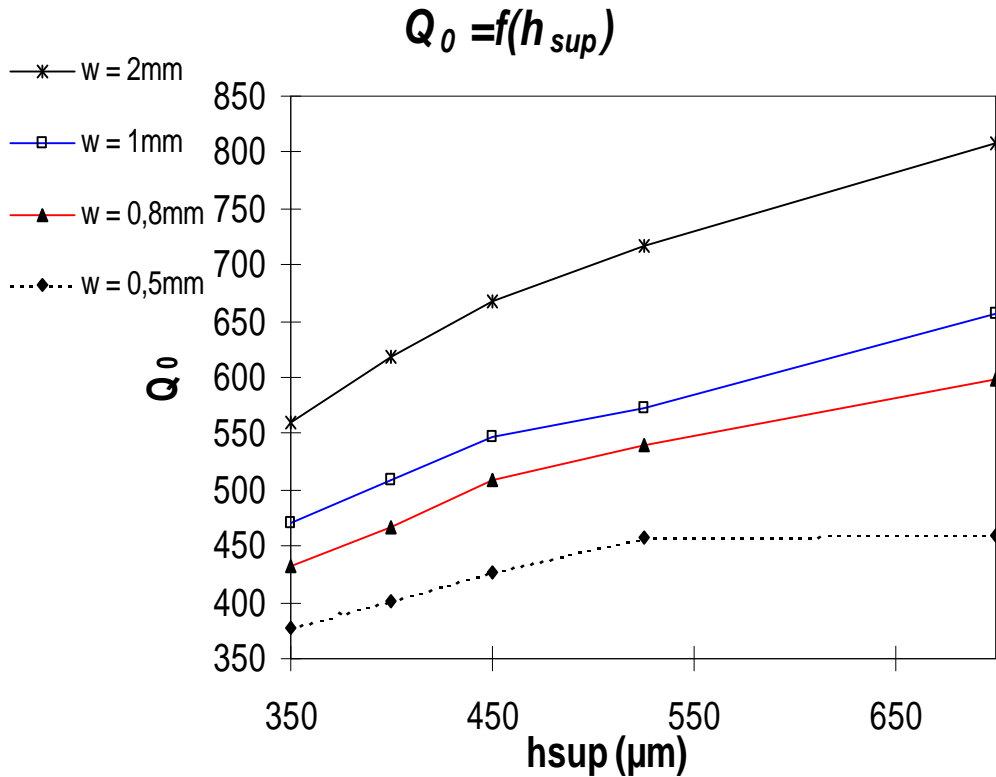
Elimination of the resin



Selective etching of Si until the membrane is released

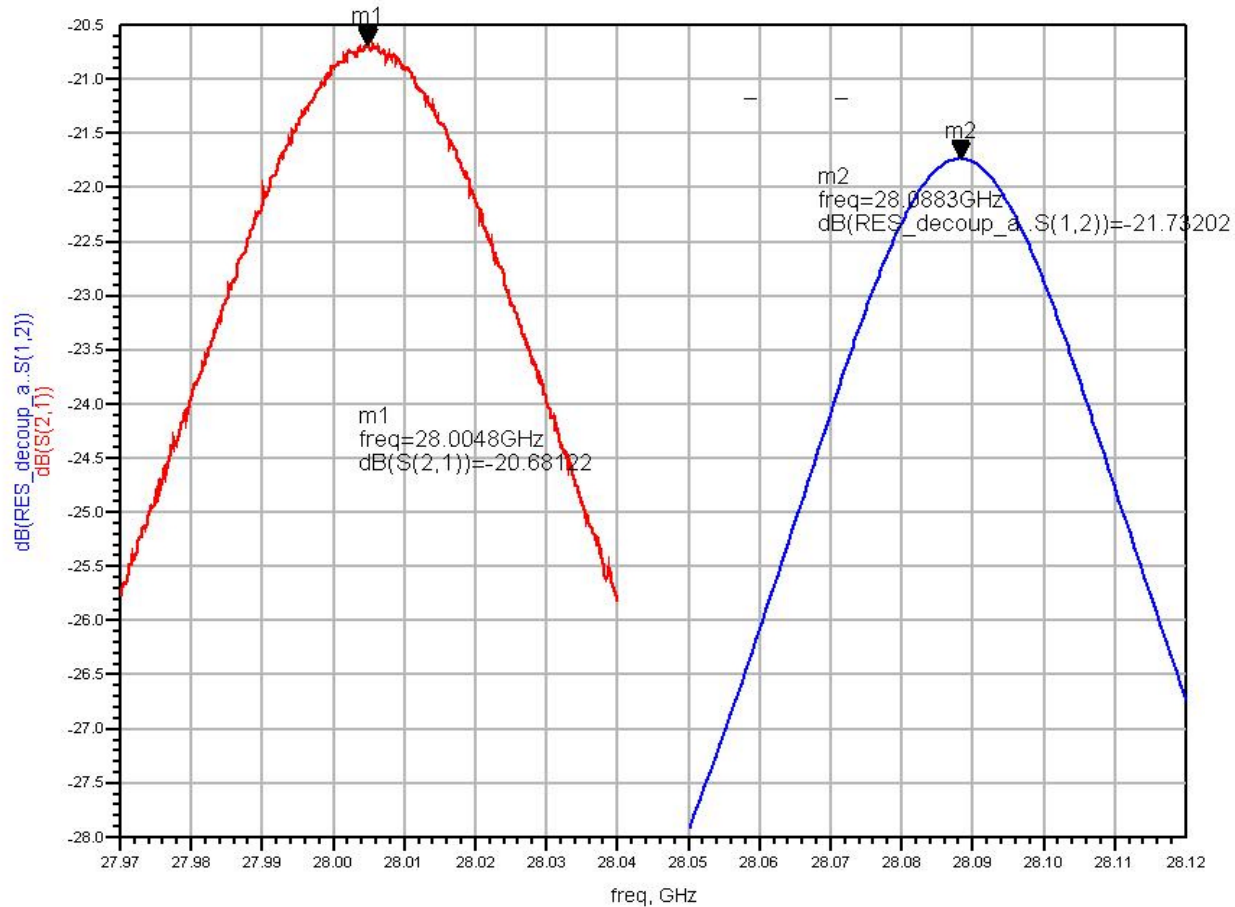
DIMENSION AND RESONATOR OPTIMIZATION

COMPUTED WITH
ADS MOMENTUM



$$\left\{ \begin{array}{l} \mathbf{W = 2 \text{ mm}} \\ \mathbf{h_{sup} = 0.425 \text{ mm}} \\ \mathbf{h_{inf} = 0.76 \text{ mm}} \end{array} \right.$$

Q₀ MEASUREMENTS - 28 GHz



$$Q_0 \text{ mes} = 602$$

$$a = 0.0042 \text{ dB/mm}$$

$$Q_0 \text{ sim} = 657$$

$$Df = 0.2\%$$

NARROW BAND MICRO-MACHINED FILTER - 28 GHz

3 POLES

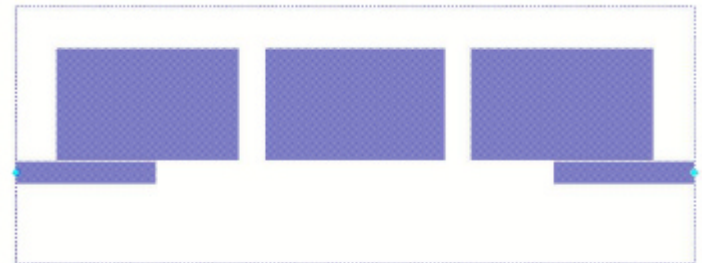
HALF WAVELENGTH RESONATORS

$$f_{\min} = 27.5 \text{ GHz}$$

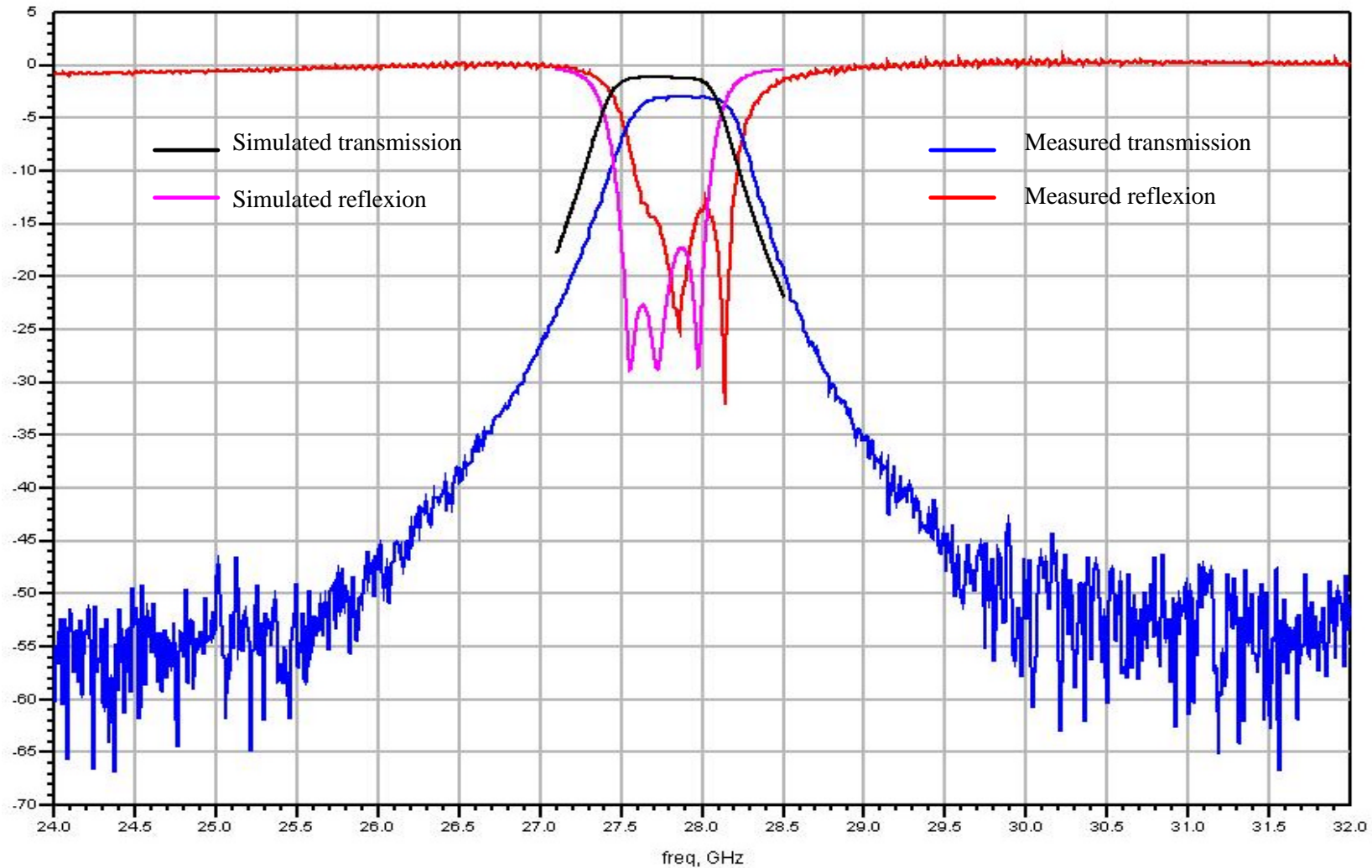
$$Df_{\min} = 500 \text{ MHz (1.8\%)}$$

HIGH REJECTION NEEDED (50 dB)

Filter scheme



FILTER MEASUREMENTS



MEASUREMENT RESULTS

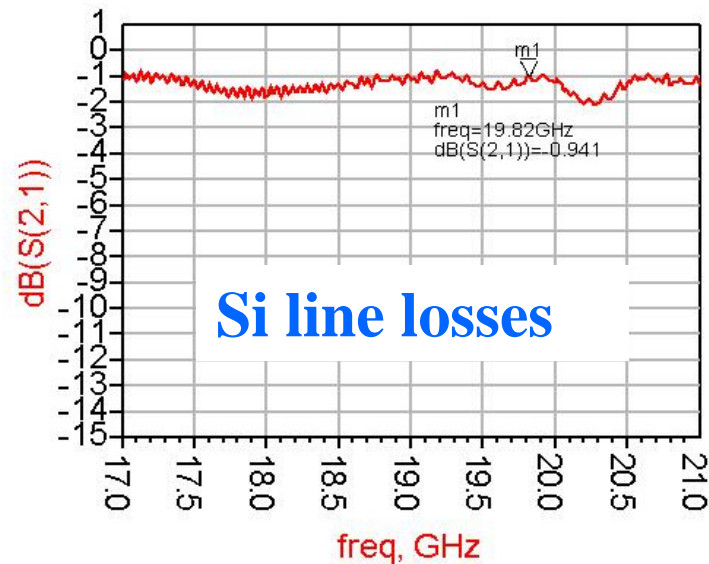
VERY GOOD MATCHING (13.5 dB)

FREQUENCY SHIFT (meas/sim)= 0.4%

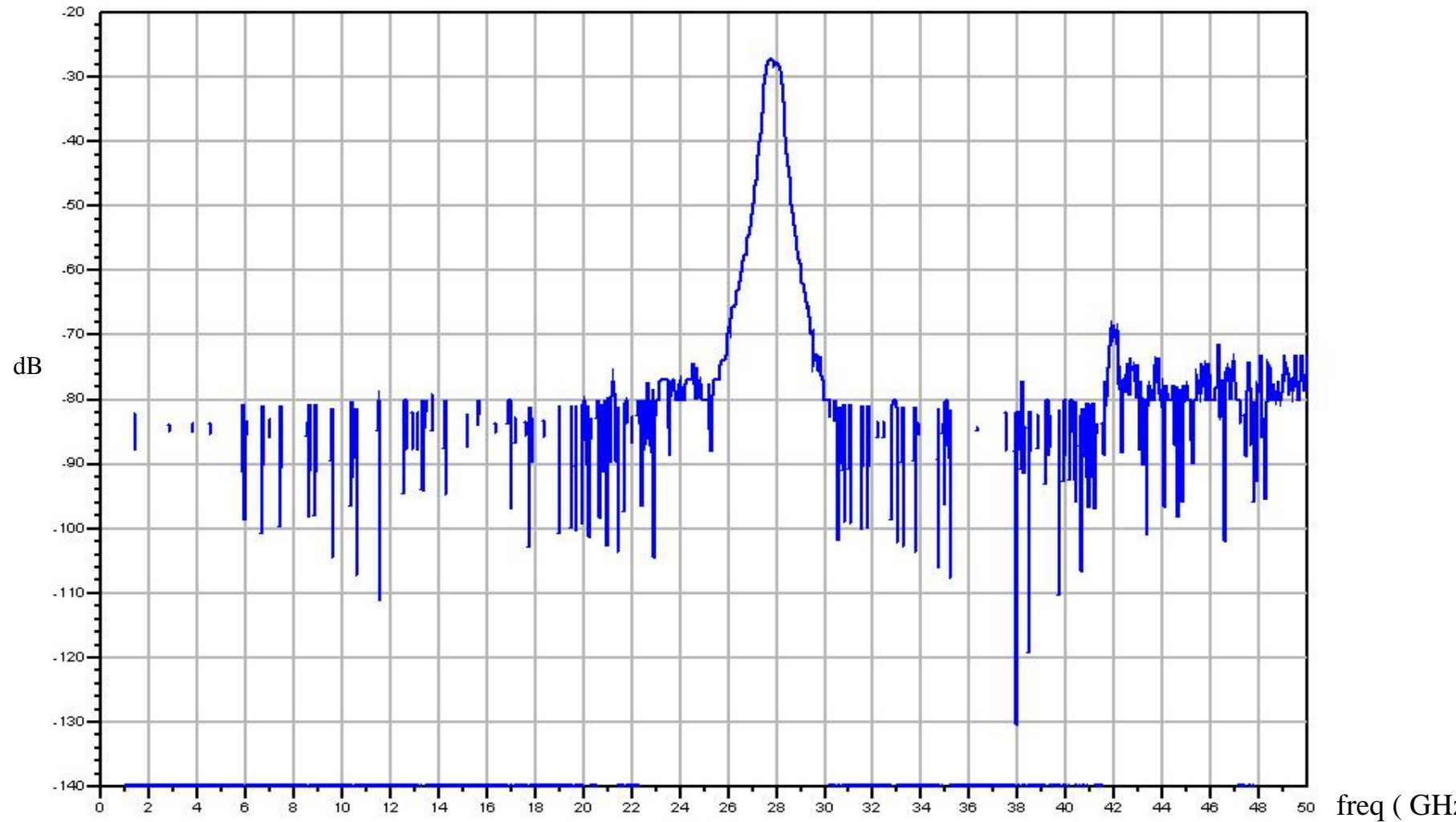
INSERTION LOSSES = 2.9 dB (1.2 dB_{theo} +1 dB line)

HIGH REJECTION (50 dB)

VERIFIED BAND-WIDTH



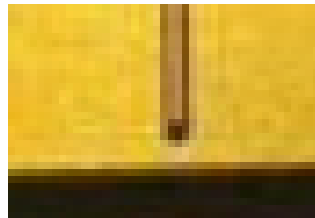
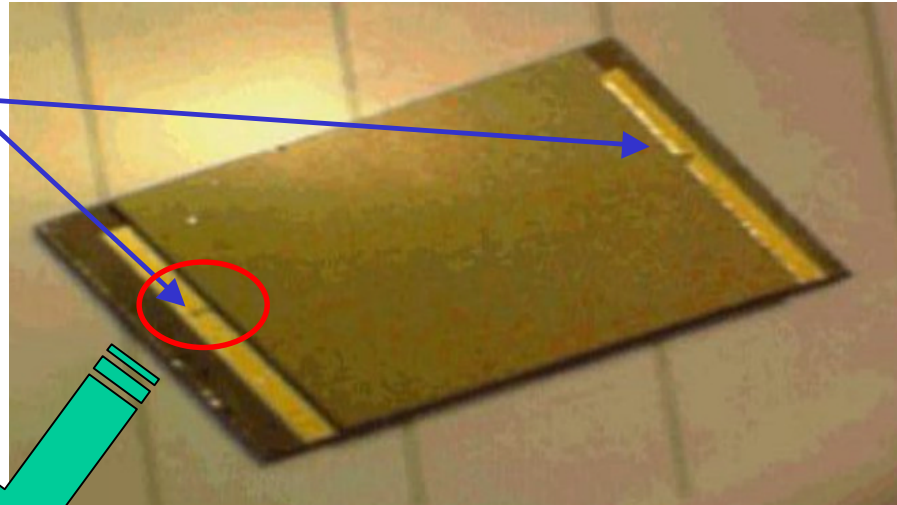
MEASUREMENT WITHOUT CALIBRATION



HIGH FREQUENCY ISOLATION

FILTER REPORT

FILTER ACCESSES



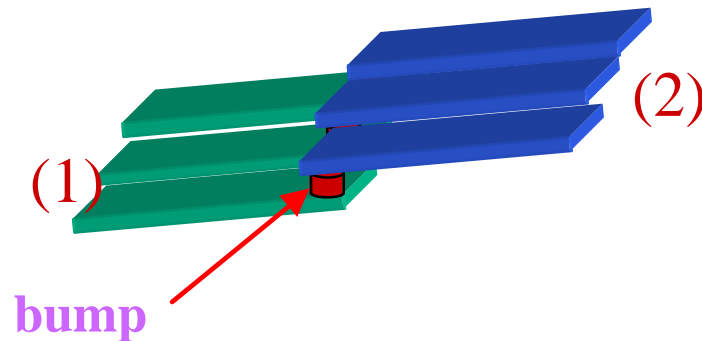
**TARGET : ACCESSES ON THE TOP WAFER
TO AVOID TRANSITION**

GOOD IMPROVEMENT

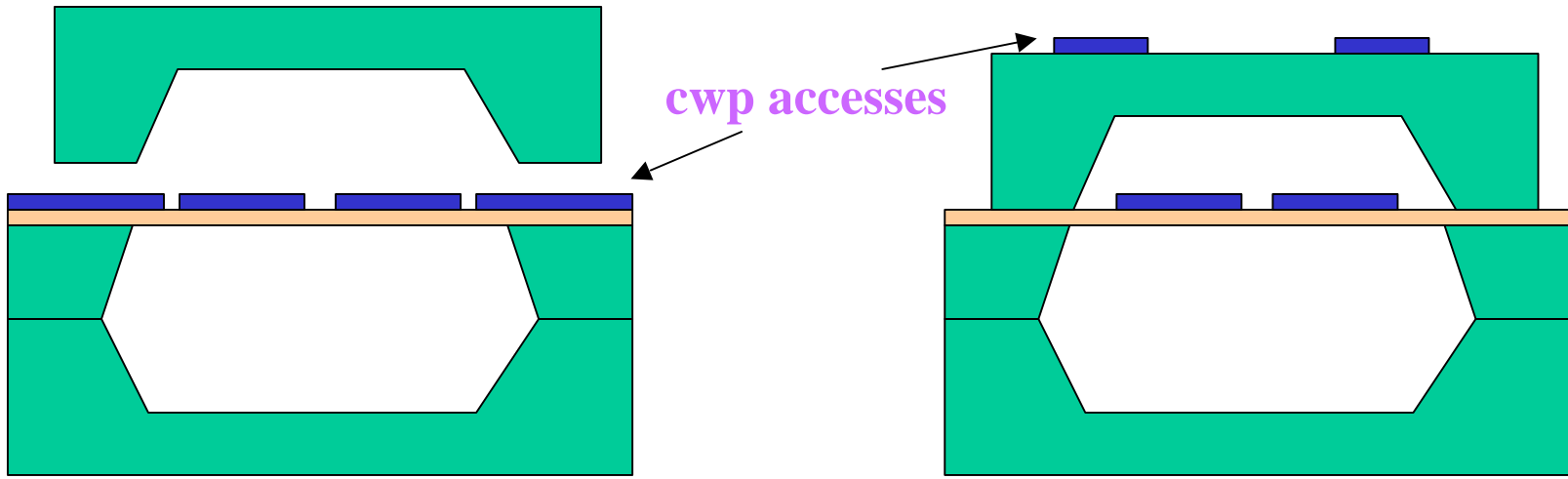
SURFACE MOUNTABLE FILTER

CPW ACCESSES ON THE TOP OF THE STRUCTURE

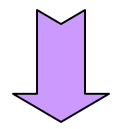
FLIP - CHIP REPORT



COMPARISON CLASSICAL/PROPOSED TOPOLOGY



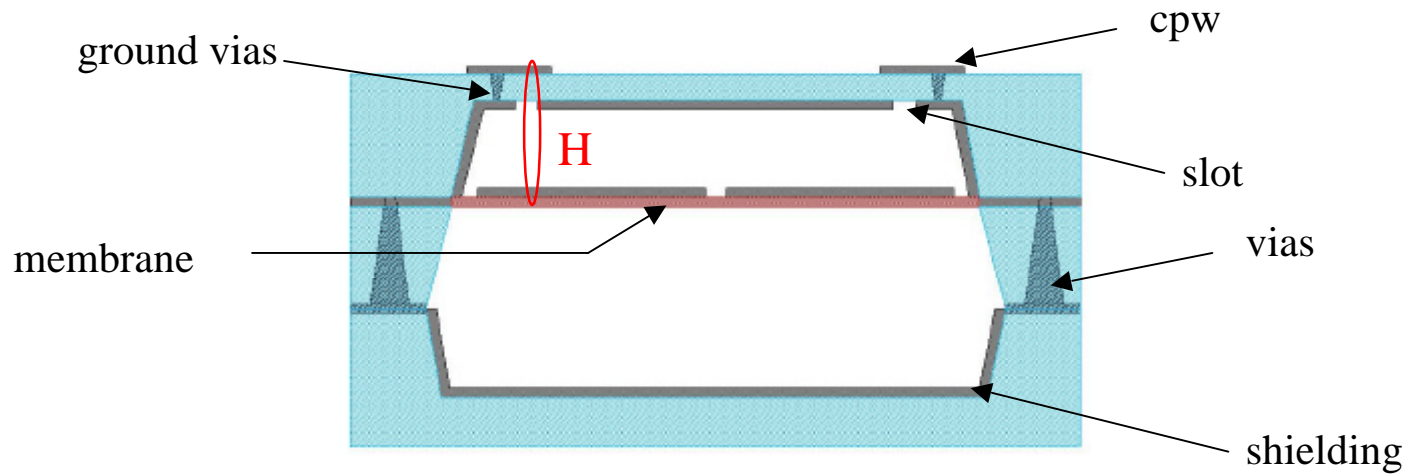
Wire bonding or transition to compensate the height of the upper cavity



LOSSES

EASY REPORT

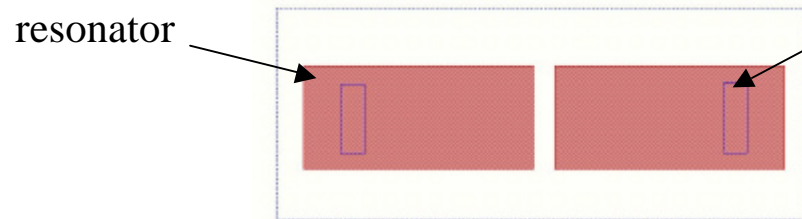
DETAILS OF THE PROPOSED STRUCTURE



Cross section

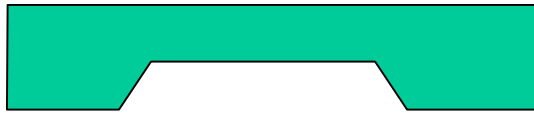


Top level

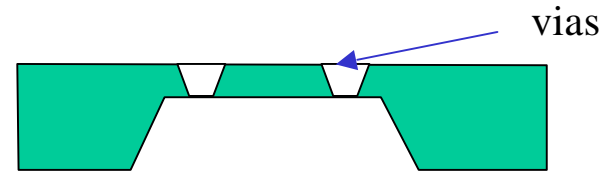


Membrane area

TOP WAFER PROCESS

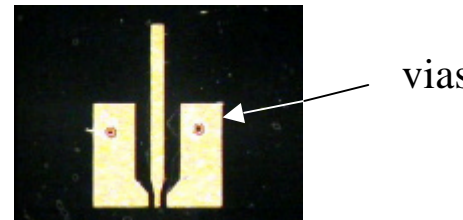


BOTTOM ETCHING 200 μm

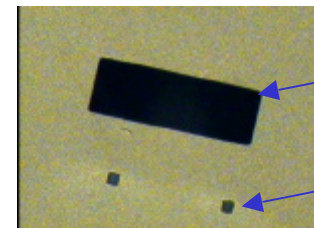
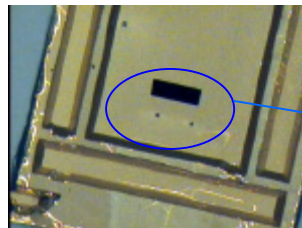


VIAS + BOTTOM ETCHING

FABRICATION OF THE UPPER CPW ACCESSES



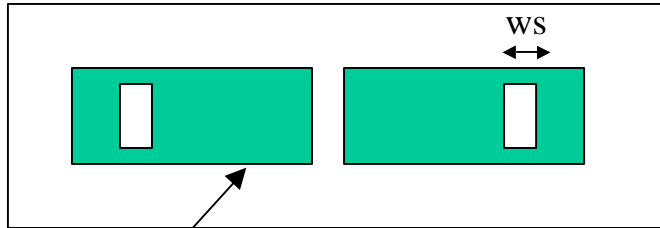
FABRICATION OF THE SLOTS TO FEED THE FILTER



slot

vias

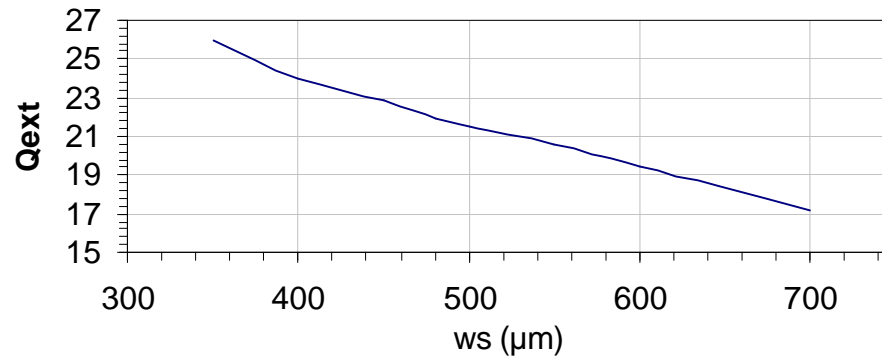
INPUT / OUTPUT COUPLING



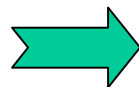
resonator

THE FEEDING OF RESONATORS
DEPENDS ON THE SLOTS DIMENSIONS

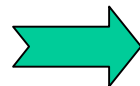
$$Q_{ext} = f(\text{slot})$$



TO INCREASE THE INPUT/OUTPUT COUPLING

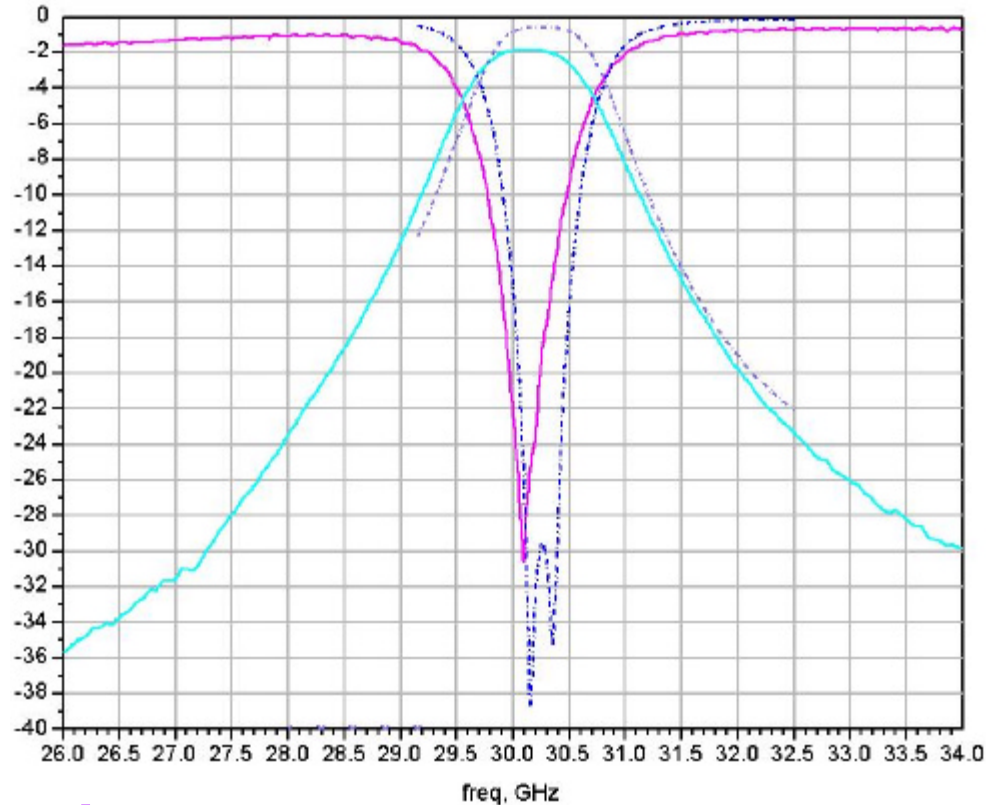


INCREASE THE SIZE OF THE SLOTS



H LOOP COUPLES MORE THE RESONATORS

SIMULATIONS/MEASUREMENTS COMPARISON



simulations

$$h_{\text{ins}} = 0.8\text{dB}$$

$$f_0 = 30.3 \text{ GHz}$$

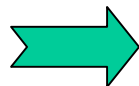
$$Df = 500 \text{ MHz}$$

measurements

$$h_{\text{ins}} = 1.8\text{dB}$$

$$f_0 = 30.1 \text{ GHz}$$

$$Df = 450 \text{ MHz}$$



GOOD AGREEMENT

CONCLUSIONS / PERSPECTIVES

**PRESENTATION OF A NARROW MICRO-MACHINED
BAND-PASS FILTER**

3 POLES WITH HIGH REJECTION

**DESIGN AND FABRICATION OF A SURFACE
MOUNTABLE MICRO-MACHINED FILTER**

EASILITY OF REPORT

GOOD AGREEMENT SIMULATIONS/MEASUREMENTS

2 POLE FILTER AT 30 GHz

POSSIBILITY TO ACHIEVE COARSER FILTER